

**AMENDMENTS TO THE SPECIFICATION**

Please add the following new paragraph and heading after the Title on page 1:

**CROSS REFERENCE TO RELATED APPLICATION**

The present application is a divisional of U.S. Application Serial No. 09/275,815 filed March 25, 1999, now U.S. Patent No. 6,642,611 issued November 4, 2003, the disclosure of which is incorporated herein by reference in its entirety.

Please replace paragraph [0031] with the following amended paragraph:

[0031] The present invention is also suitable for a process of wafer-level, as shown in FIG. 3A to FIG. 3E. In FIG. 3A, the first plurality of contact pads 11 and the second plurality of contact pads 40 are on a first surface of a substrate 20, a plurality of connection pads 21 is on a second surface of the substrate 20, and the first contact pads 11 and the connection pads 21 are connected with each other through the via holes 31. Then, a buffer layer 30 is formed on the substrate 20, and the part of the buffer layer 30 except on the second contact pads 40 is removed to form the plurality of openings 90, as shown in FIG. 3B. After that, the electronic devices 10 respectively correspond to openings 90 and are mounted on the buffer layer, as shown in FIG. 3C, and the buffer layer 30 supports the edges of the electronic devices 10, as shown in FIG. 3D. A cutting process may be proceeded for dividing into each of the electronic devices 10, as shown in FIG. 3E. The cutting process may be a half cut, so as to match the demand for successive processes. It is to be noted that the buffer layers 30 in FIG. 3D and FIG. 3E are different in shape from that of the buffer layer 30 shown in FIG. 3C. In FIG. 3D and FIG. 3E, since the buffer layer 30 has been subject to the force 60 at a specific portion thereof, which will be discussed below, it becomes like a shoulder having a first part 34 with a first surface 32, a second part 35 with a second surface 33 and a corner 36. The first part 34 has a first density and the second part 35 has a second density, which is greater than the first density since the second part 35 has been subject to the force 60 while the first part 34 has not been pressed. In this case, the buffer layer 30 may not only provide the self-planarization

function as mentioned above for the electronic device 10 at the second part 35 but also provide the hermetical sealing result at the first part 34 (also mentioned above) concurrently.

Please replace paragraph [0032] with the following amended paragraph:

[0032] The another preferred embodiment of the present invention is as shown in FIG. 4. Compared with the aforementioned structure, a conductive layer 50 is formed on the electronic device 10, the buffer layer 30, and the second plurality of contact pads 40. The conductive layer 50 has the function of shielding from electromagnetism wave and increasing the hermeticity. Likewise, the buffer layer 40 in FIG. 4 is formed like a shoulder having a first part 44 with a first surface 42, a second part 45 with a second surface 43 and a corner 46. The first part 44 has a first density and the second part 45 has a second density, which is greater than the first density. In this case, the buffer layer 30 may not only provide the self-planarization function as mentioned above for the electronic device 10 at the second part 45 but also provide the hermetical sealing result at the first part 44 (also mentioned above) concurrently.

Please add the following new paragraph after paragraph [0032]:

[0032.1] Typically, the solder 16 has a height of 50 microns before being pressed by the force 60 and 30 to 40 microns after being pressed and each of the pads 11 has the considerable height value. Therefore, in a preferred embodiment, the buffer layer 30 is set as 30 to 200 microns in thickness, both the first part 44 and second part 45 are alike but with a height difference.